Xutao Zhang

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/124273/publications.pdf

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18	470	759233 12	888059 17
papers	citations	h-index	g-index

19	19	19	629
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	A New Strategy for Selective Area Growth of Highly Uniform InGaAs/InP Multiple Quantum Well Nanowire Arrays for Optoelectronic Device Applications. Advanced Functional Materials, 2022, 32, 2103057.	14.9	21
2	A New Strategy for Selective Area Growth of Highly Uniform InGaAs/InP Multiple Quantum Well Nanowire Arrays for Optoelectronic Device Applications (Adv. Funct. Mater. 3/2022). Advanced Functional Materials, 2022, 32, .	14.9	1
3	Self-frequency-conversion nanowire lasers. Light: Science and Applications, 2022, 11, 120.	16.6	13
4	Gateâ€Switchable Photovoltaic Effect in BP/MoTe₂ van der Waals Heterojunctions for Selfâ€Driven Logic Optoelectronics. Advanced Optical Materials, 2021, 9, 2001802.	7.3	32
5	Photoelectronic Properties of End-bonded InAsSb Nanowire Array Detector under Weak Light. Nanoscale Research Letters, 2021, 16, 13.	5.7	3
6	Axiotaxy driven growth of belt-shaped InAs nanowires in molecular beam epitaxy. Nano Research, 2021, 14, 2330.	10.4	0
7	Ultralow Threshold, Single-Mode InGaAs/GaAs Multiquantum Disk Nanowire Lasers. ACS Nano, 2021, 15, 9126-9133.	14.6	19
8	Selective area epitaxy of IIIâ€“V nanostructure arrays and networks: Growth, applications, and future directions. Applied Physics Reviews, 2021, 8, .	11.3	75
9	MoTe₂ PN Homojunction Constructed on a Silicon Photonic Crystal Cavity for High-Performance Photodetector. ACS Photonics, 2021, 8, 2431-2439.	6.6	22
10	Thickness-Controlled Three-Dimensional Dirac Semimetal for Scalable High-Performance Terahertz Optoelectronics. ACS Photonics, 2021, 8, 1689-1697.	6.6	16
11	Anomalous Photoelectrical Properties through Strain Engineering Based on a Single Bent InAsSb Nanowire. ACS Applied Materials & Interfaces, 2021, 13, 5691-5698.	8.0	6
12	Auâ€“InSe van der Waals Schottky junctions with ultralow reverse current and high photosensitivity. Nanoscale, 2020, 12, 4094-4100.	5.6	31
13	High-quality epitaxial wurtzite structured InAs nanosheets grown in MBE. Nanoscale, 2020, 12, 271-276.	5.6	10
14	Surface-States-Modulated High-Performance InAs Nanowire Phototransistor. Journal of Physical Chemistry Letters, 2020, 11, 6413-6419.	4.6	21
15	Light-Induced Positive and Negative Photoconductances of InAs Nanowires toward Rewritable Nonvolatile Memory. ACS Applied Electronic Materials, 2019, 1, 1825-1831.	4.3	14
16	Free-Standing InAs Nanobelts Driven by Polarity in MBE. ACS Applied Materials & Interfaces, 2019, 11, 44609-44616.	8.0	6
17	Ultrasensitive Mid-wavelength Infrared Photodetection Based on a Single InAs Nanowire. ACS Nano, 2019, 13, 3492-3499.	14.6	45
18	Visible Light-Assisted High-Performance Mid-Infrared Photodetectors Based on Single InAs Nanowire. Nano Letters, 2016, 16, 6416-6424.	9.1	134